Docket No.

241098US2SRD

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF:

Mizuki ONO, et al.

SERIAL NO: NEW APPLICATION

GAU:

FILED:

HEREWITH

EXAMINER:

FOR:

SEMICONDUCTOR DEVICE

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR 1.97

COMMISSIONER FOR PATENTS ALEXANDRIA, VIRGINIA 22313

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- Each item of information contained in this information disclosure statement was first cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND. MAIER & NEUSTADT, P.C.

Marvin J. Spivak

Registration No. 24,913

C. Irvin McClelland Registration Number 21,124

Tel. (703) 413-3000 Fax. (703) 413-2220 (OSMMN 05/03)

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LIST OF RELATED CASES

	Serial or	Filing or	Inventor/		
Docket Number	Patent Number	Issue Date	Applicant		
210313US2 SRD	09/891,129	06/26/01	NISHIYAMA et al.		

DOCKET NO: 241098US2SRD

Sheet __1_ of __1

IN RE APPLICATION OF: Mizuki ONO, et al.

SERIAL NO: New Application

FILED: Herewith

L

FOR: SEMICONDUCTOR DEVICE

STATEMENT OF RELEVANCY

Reference AO (JP 2002-16063) on Form PTO- 1449:

TiO₂ micro-crystals formed in Ti-Si-O gate dielectric of MISFETs by high-temperature annealing.

Reference AP (JP 2000-307010) on Form PTO- 1449:

Integrated circuits containing transistors, gate dielectrics of which are made of 2 kinds of materials.

Reference AX on Form PTO-1449:

Compositional dependences of the crystallization temperature of some high permittivity thin films are shown.

Form PTO 1449 U.S. DEPARTMENT OF COMMERCE (Modified) PATENT AND TRADEMARK OFFICE		ATTY DOCKET NO. 241098US2SRD		SERIAL NO. NEW APPLICATION							
		APPLICANT TELEVISION APPLICANT									
LIST OF REFERENCES CITED BY APPLICANT		Mizuki ONO, et al.									
				FILING DATE		GROUP					
		HEREWITH									
U.S. PATENT DOCUMENTS											
EXAMINER	_	DOCUMENT			SUB FILING DATE						
INITIAL		NUMBER	DATE	NAME	CLASS	CLASS IF APPROPRIATE					
	AA										
	AB										
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		DOCUMENT NUMBER	DATE	COUNTRY		TRANS		LATION NO			
	AO	2002-16063	01/18/02	Japan				×			
	AP	2000-307010	11/02/02	Japan				×			
	AQ										
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	AV					<u> </u>					
		OTHER R	EFERENCES	(Including Author, Title, Date, Pertinen	t Pages, e	tc.)					
	G. LUCOVSKY, et al., "Microscopic Model for Enhanced Dielectric Constants in Low Concentration SiO ₂ -Rich Noncrystalline AW Zr and Hf Silicate Alloys", APPLIED PHYSICS LETTERS, Vol. 77, No. 18, October 30, 2000, pgs. 2912-2914										
	AX	Angus I. KINGON, et al., "Alternative Dielectrics to Silicon Dioxide for Memory and Logic Devices", NATURE, Vol. 406, August 31, 2000, pgs. 1032-1038									
	AY										
	AZ		****	Additional References sheet(s) attached							
Examiner					Date Co	Date Considered					
*Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.											